

# BogusÅ,awa Adamowicz

## List of Publications by Year in descending order

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39  
papers

894  
citations

567281

15  
h-index

454955

30  
g-index

39  
all docs

39  
docs citations

39  
times ranked

1105  
citing authors

#	ARTICLE	IF	CITATIONS
1	Origin of positive fixed charge at insulator/AlGa <sub>N</sub> interfaces and its control by AlGa <sub>N</sub> composition. Applied Physics Letters, 2017, 110, 243505.	3.3	19
2	Disorder induced gap states as a cause of threshold voltage instabilities in Al <sub>2</sub> O <sub>3</sub> /AlGa <sub>N</sub> /Ga <sub>N</sub> metal-oxide-semiconductor high-electron-mobility transistors. Journal of Applied Physics, 2017, 122, .	2.5	16
3	On the origin of interface states at oxide/III-nitride heterojunction interfaces. Journal of Applied Physics, 2016, 120, .	2.5	41
4	Characterization of capture cross sections of interface states in dielectric/III-nitride heterojunction structures. Journal of Applied Physics, 2016, 119, .	2.5	21
5	A novel method for the determination of the full energetic distribution of interface state density in metal/insulator/GaN structures from capacitance - voltage and photocapacitance - light intensity measurements. , 2013, , .		0
6	Determination of the deep donor-like interface state density distribution in metal/Al <sub>2</sub> O <sub>3</sub> /n-GaN structures from the photocapacitanceâ€“light intensity measurement. Applied Physics Letters, 2012, 101, .	3.3	24
7	Role of interface states and depletion layer in NO <sub>2</sub> sensing mechanism of n-InP epitaxial layers. Sensors and Actuators A: Physical, 2012, 181, 43-50.	4.1	2
8	Surface photovoltage and Auger electron spectromicroscopy studies of HfO <sub>2</sub> /SiO <sub>2</sub> /4H-SiC and HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> /4H-SiC structures. Applied Surface Science, 2012, 258, 8354-8359.	6.1	14
9	The influence of interface states and bulk carrier lifetime on the minority carrier behavior in an illuminated metal/insulator/GaN structure. Solid State Communications, 2011, 151, 830-833.	1.9	0
10	Impact of Interface States and Bulk Carrier Lifetime on Photocapacitance of Metal/Insulator/GaN Structure for Ultraviolet Light Detection. Japanese Journal of Applied Physics, 2011, 50, 04DF08.	1.5	2
11	Surface passivation of IIIâ€“V semiconductors for future CMOS devicesâ€“Past research, present status and key issues for future. Applied Surface Science, 2010, 256, 5698-5707.	6.1	63
12	Capacitance-voltage and photoluminescence study of high-kâ€“GaAs interfaces controlled by Si interface control layer. Journal of Vacuum Science & Technology B, 2009, 27, 2028.	1.3	6
13	Surface electronic properties of sulfur-treated GaAs determined by surface photovoltage measurement and its computer simulation. Surface Science, 2009, 603, 498-502.	1.9	18
14	Simulations of Capacitanceâ€“Voltageâ€“Temperature Behavior of Metal/Insulator/AlGa <sub>N</sub> and Metal/Insulator/AlGa <sub>N</sub> /Ga <sub>N</sub> Structures. Japanese Journal of Applied Physics, 2009, 48, 04C092.	1.5	32
15	A novel IIIâ€“V semiconductor material for NO <sub>2</sub> detection and monitoring. Sensors and Actuators A: Physical, 2008, 142, 237-241.	4.1	11
16	Surface state density distribution at vacuum-annealed InP(100) surface as derived from the rigorous analysis of photoluminescence efficiency. Applied Surface Science, 2008, 254, 8046-8049.	6.1	5
17	Response to oxygen and chemical properties of SnO <sub>2</sub> thin-film gas sensors. Vacuum, 2008, 82, 966-970.	3.5	22
18	Effects of interface states and temperature on the C-V behavior of metal/insulator/AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructure capacitors. Journal of Applied Physics, 2008, 103, .	2.5	172

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19	Computer analysis of an influence of oxygen vacancies on the electronic properties of the SnO <sub>2</sub> surface and near-surface region. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 2241-2246.	1.8	12
20	XPS, electric and photoluminescence-based analysis of the GaAs (100) nitridation. <i>Applied Surface Science</i> , 2006, 252, 7890-7894.	6.1	10
21	Room temperature photoluminescence studies of nitrided InP(100) surfaces. <i>Materials Science and Engineering C</i> , 2006, 26, 378-382.	7.3	0
22	Dynamics and control of recombination process at semiconductor surfaces, interfaces and nano-structures. <i>Solar Energy</i> , 2006, 80, 629-644.	6.1	20
23	Rigorous analysis of the electronic properties of InP interfaces for gas sensing. <i>Thin Solid Films</i> , 2003, 436, 101-106.	1.8	3
24	Rigorous analysis of photoluminescence efficiency for characterisation of electronic properties of InP(100) surfaces. <i>Vacuum</i> , 2002, 67, 3-10.	3.5	5
25	XPS study of the L-CVD deposited SnO <sub>2</sub> thin films exposed to oxygen and hydrogen. <i>Thin Solid Films</i> , 2001, 391, 198-203.	1.8	216
26	Computer analysis of photoluminescence efficiency at InP surface with U-shaped surface state continuum. <i>Vacuum</i> , 2001, 63, 223-227.	3.5	9
27	Computer analysis of photon-induced non-equilibrium phenomena at Si and AlGaAs surfaces. <i>Vacuum</i> , 2000, 57, 111-120.	3.5	4
28	Analysis of photoluminescence efficiency and surface recombination velocity of MBE-grown AlGaAs layers. <i>Thin Solid Films</i> , 2000, 367, 180-183.	1.8	7
29	The comparative XPS and PYS studies of SnO <sub>2</sub> thin films prepared by L-CVD technique and exposed to oxygen and hydrogen. <i>Sensors and Actuators B: Chemical</i> , 2000, 70, 177-181.	7.8	57
30	Computer simulations of the surface photovoltage on Si and GaAs surfaces with U-shaped surface state continuum. <i>Vacuum</i> , 1999, 54, 173-177.	3.5	4
31	Electronic properties of Al <sub>x</sub> Ga <sub>1-x</sub> As surface passivated by ultrathin silicon interface control layer. <i>Applied Surface Science</i> , 1999, 141, 326-332.	6.1	3
32	Photoluminescence characterization of air exposed AlGaAs surface and passivated ex situ by ultrathin silicon interface control layer. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 261-266.	2.7	8
33	Computer Analysis of Surface Recombination Process at Si and Compound Semiconductor Surfaces and Behavior of Surface Recombination Velocity. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 1631-1637.	1.5	36
34	Inverse photoemission and Kelvin probe studies of the Au/GaP(110) interface. <i>Vacuum</i> , 1995, 46, 509-512.	3.5	0
35	Dependence of silicon surface electronic parameters on surface Fermi level position. <i>Vacuum</i> , 1994, 45, 167-170.	3.5	1
36	Near-band gap transitions in the surface photovoltage spectra for GaAs, GaP and Si surfaces. <i>Surface Science</i> , 1991, 247, 94-99.	1.9	19

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37	Investigation of electron processes at the p and n type Si(111) real surface by the surface photovoltage method. Surface Science, 1990, 231, 1-8.	1.9	9
38	The contribution of surface effects to the surface photovoltage dependence on temperature for the real Si(111) surface. Surface Science, 1988, 200, 172-178.	1.9	3
39	Electronic Properties of the Clean and Oxygen Exposed GaAs(100) Surface. Studies in Surface Science and Catalysis, 1988, 40, 229-231.	1.5	0